

isc Silicon NPN Power Transistor

BUV48A

DESCRIPTION

- · High Voltage Capability
- · High Current Capability
- · Fast Switching Speed

APPLICATIONS

Designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particulary suited for line-operated swtchmode applications such as:

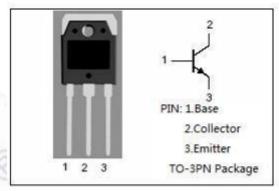
- · Switching regulators
- Inverters
- · Solenoid and relay drivers
- Motor controls
- Deflection circuits

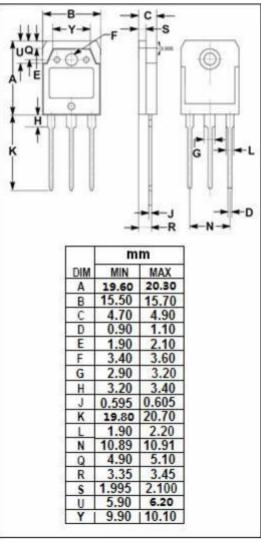
Absolute maximum ratings(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------------|
| Vcex | Collector-Emitter Voltage (V _{BE} = -1.5V) | 1000 | V |
| Vceo | Collector-Emitter Voltage | 450 | V |
| Vево | Emitter-Base Voltage | 7 | V |
| lc | Collector Current-Continuous | 15 | Α |
| Ісм | Collector Current-Peak | | Α |
| I в | Base Current-Continuous | 5 | Α |
| Івм | Base Current-peak | 20 | Α |
| Pc | Collector Power Dissipation @Tc=25℃ | 150 | W |
| Tj | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -65~150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------|-------------------------------------|-----|------|
| Rth j-c | Thermal Resistance,Junction to Case | 1.0 | °C/W |







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ELECTRICAL CHARACTERISTICS

Tc=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|-------------------------|--------------------------------------|---|-----|-----|------|
| V _{CEO(SUS)} | Collector-Emitter Sustaining Voltage | Ic= 30mA; I _B = 0 | 450 | | V |
| $V_{(BR)EBO}$ | Emitter-Base Breakdown Voltage | I _E = 10mA; I _C = 0 | 7 | | ٧ |
| V _{CE} (sat)-1 | Collector-Emitter Saturation Voltage | Ic= 8A; Iв= 1.6A | | 1.5 | ٧ |
| V _{CE} (sat)-2 | Collector-Emitter Saturation Voltage | Ic= 12A ;I _B = 2.4A | | 5.0 | V |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | Ic= 8A; I _B = 1.6A | | 1.6 | V |
| Ісео | Collector Cutoff Current | V _{CE} =450V, IB=0 | | 0.5 | mA |
| Ісво | Collector Cutoff Current | V _{CB} =850V IE=0 | | 0.2 | mA |
| І ЕВО | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | 0.1 | mA |
| hfE | DC Current Gain | Ic= 8A ; VcE= 5V | 8 | | |

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